

Supporting information for:

Tuning Molecule Diffusion to Control the Phase Separation of *p*-DTS(FBTTh₂)₂/EP-PDI Blend System via Thermal Annealing

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Fig. S1

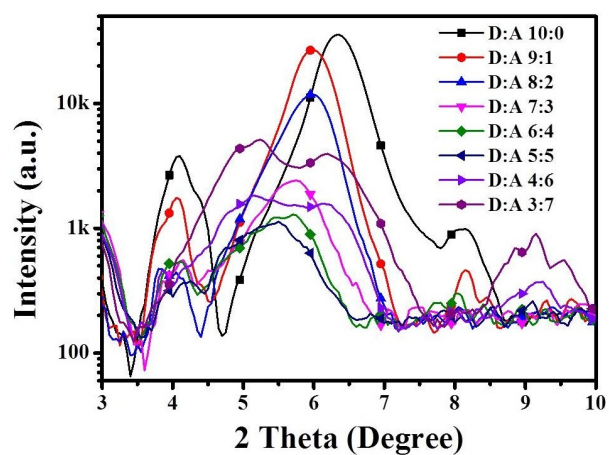
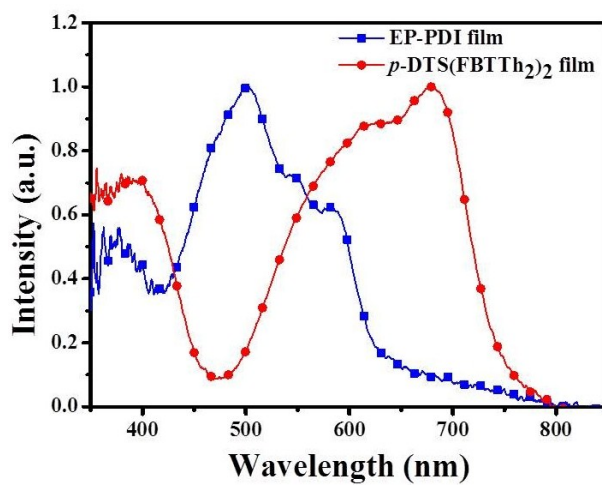
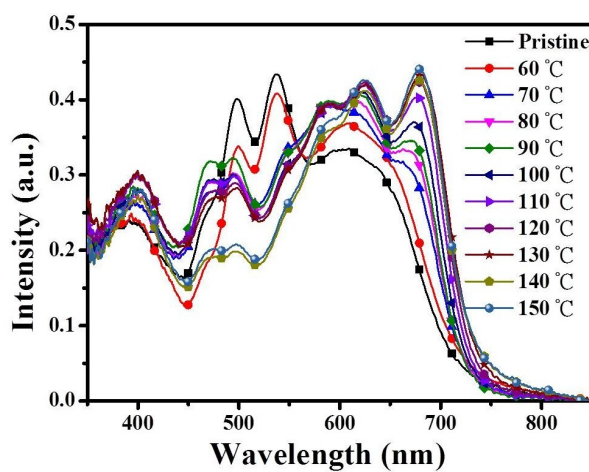


Fig. S1 1D out-of-plane X-ray profiles of blend films with different *p*-DTS(FBTTh₂)₂/EP-PDI ratios. The obtained X-ray intensities were added 200 to avoid the minus, thus we can use log scale to enhance the visibility of weak intensity.

Fig. S2



The UV-vis absorption spectra of pure *p*-DTS(FBTTh₂)₂ and EP-PDI films.



The UV-vis absorption spectra of *p*-DTS(FBTTh₂)₂:EP-PDI 6:4 blend film thermal annealed at different temperature for 10 min.

Fig.S3

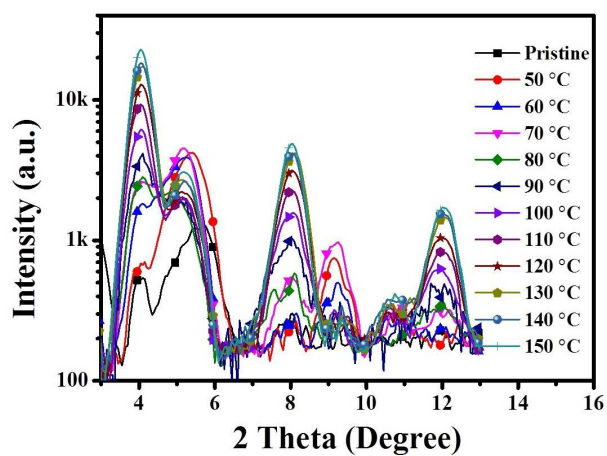


Fig. S3 Out-of-plane X-ray profiles of *p*-DTS(FBTTh₂)₂:EP-PDI blend films at 6:4 TA treated at different temperature for 10 min. The obtained X-ray intensities were added 200 to avoid the minus, thus we can use log scale to enhance the visibility of weak intensity.

Fig. S4

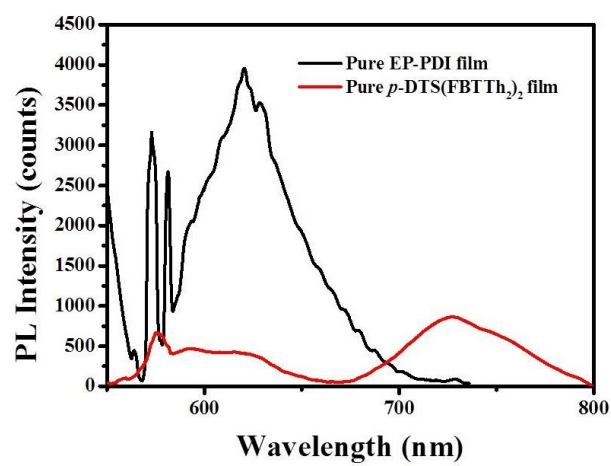
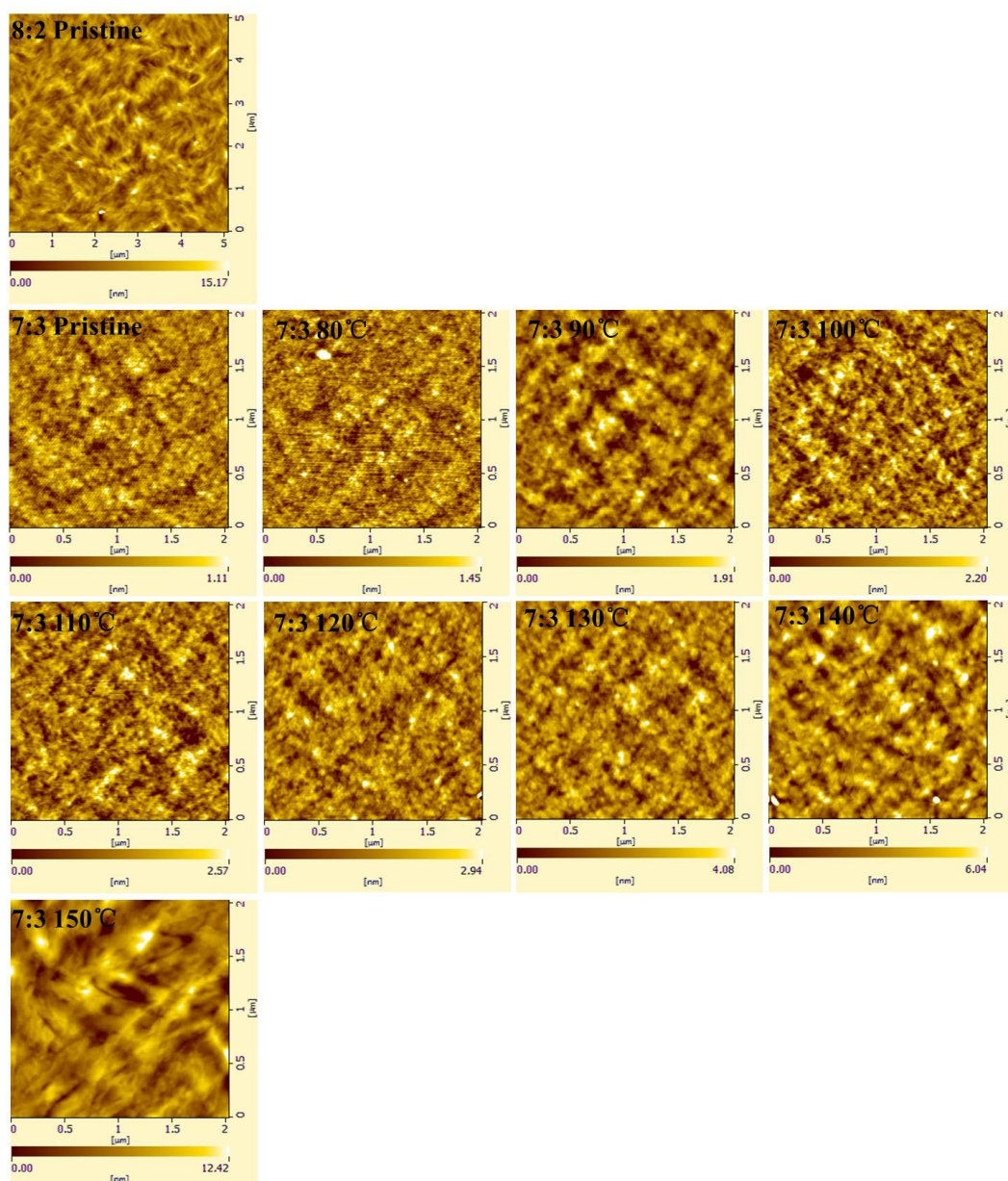


Fig. S4 Fluorescence spectra of pure *p*-DTS(FBTTh₂)₂ and EP-PDI films.

Fig. S5



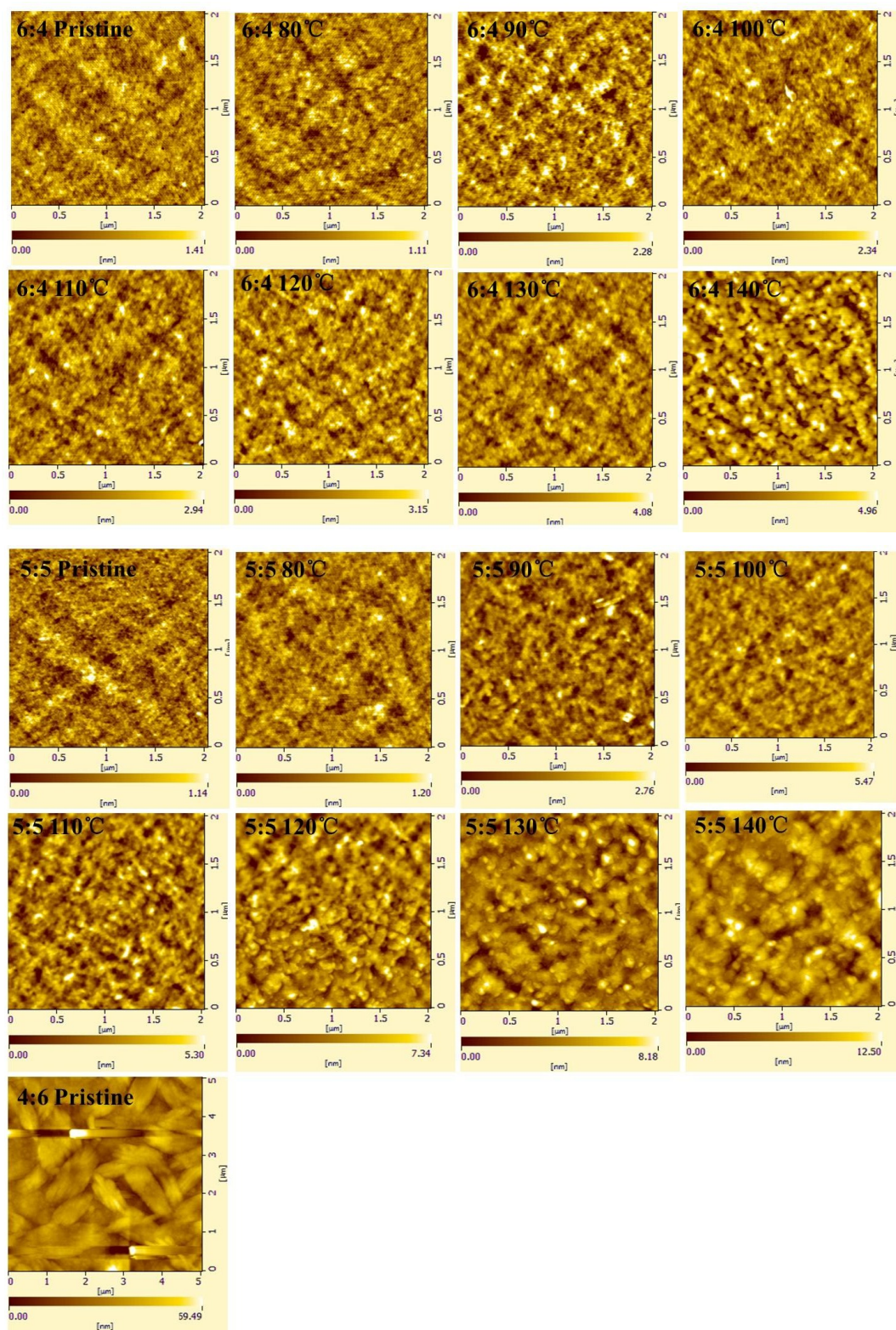


Fig. S5 The AFM images of different ratios of p -DTS(FBTTh₂)₂:EP-PDI blend film thermal annealed at different temperature.

Table S6

D:A 5:5	V_{OC} (V)	J_{SC}(mA/cm²)	FF	PCE (%)
pristine	0.23	0.66	0.34	0.05
60 °C	0.48	1.34	0.39	0.25
70 °C	0.66	2.87	0.40	0.75
80 °C	0.69	4.98	0.45	1.54
90 °C	0.69	5.20	0.46	1.65
100 °C	0.75	7.58	0.55	3.12
110 °C	0.74	7.25	0.53	2.84
120 °C	0.57	5.92	0.39	1.31

D:A 7:3	V_{OC} (V)	J_{SC}(mA/cm²)	FF	PCE (%)
pristine	0.21	0.75	0.37	0.06
80 °C	0.47	4.95	0.38	0.88
90 °C	0.66	6.05	0.48	1.91
100 °C	0.70	7.21	0.52	2.62
110 °C	0.72	7.53	0.55	2.98
120 °C	0.74	7.73	0.55	3.15
130 °C	0.73	6.57	0.56	2.68
140 °C	0.67	6.30	0.48	2.02
150 °C	0.57	5.62	0.40	1.28

Table S6 Device parameters of *p*-DTS(FBTTh₂)₂:EP-PDI ratio of 7:3 and 5:5 TA treated at different temperature.